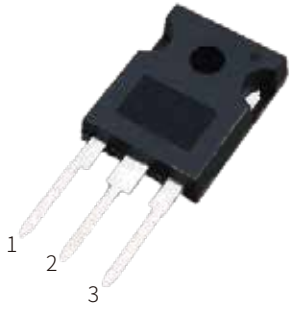
FEATURES

- Glass-passivated mesa chip for reliability and uniform
- High current output up to 60A



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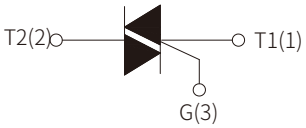
APPLICATIONS

- Motor cycle
- Power charger
- T-tools etc



Schematic Symbol

APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage (T_j=25°C)	V_{DRM}	1200	V
Repetitive peak reverse voltage (T_j=25°C)	V_{RRM}	1200	
RMS on-state current (T_C⩽87°C)	$I_{T(RMS)}$	60	A
Non repetitive surge peak on-state current (tp=20ms,T_j=25°C)	I_{TSM}	600	
I^2t value for fusing (tp=10ms,T_j=25°C)	I^2t	1800	A^2S
Critical rate of rise of on-state current (I_G=2*I_{GT},f=100Hz,T_j=125°C)	dI/dt	100	A/μs
Peak gate current (tp=20μs,T_j=125°C)	I_{GM}	10	A
Average gate power dissipation (T_j=125°C)	$P_{G(AV)}$	0.5	W
Storage junction temperature range	T_{STG}	-40~+150	°C
Operating junction temperature range	T_j	-40~+125	

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value			Unit
			Min.	Typ.	Max.	
I_{GT}	V_D=12V,R_L=33Ω	I - II - III			50	mA
V_{GT}					1.3	V
V_{GD}	V_D=V_{DRM},R_L=3.3KΩ,T_j=125°C	I - II - III	0.2			V
I_H	I_T=1A				80	mA
I_L	I_G=1.2I_{GT}	I - III			120	
		II			120	
dV_D/dt	V_D=800 Gate Open T_j=125°C		2000			V/μs
(dI/dt)c	(dV/dt)c=20V/μs T_j=125°C		25			A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25°C			7		μs
t_{off}				70		μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value	Unit
V_{TM}	I_{TM}=80A,tp=380μs	T_j=25°C	⩽1.7	V
I_{DRM}	V_D=V_{DRM}, V_R=V_{RRM}		⩽12	μA
I_{RRM}		T_j=125°C	⩽8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case(AC)	0.32	°C/W

PARAMETER CHARACTERISTIC CURVE

FIG.1 Maximum power dissipation versus RMS on-state current

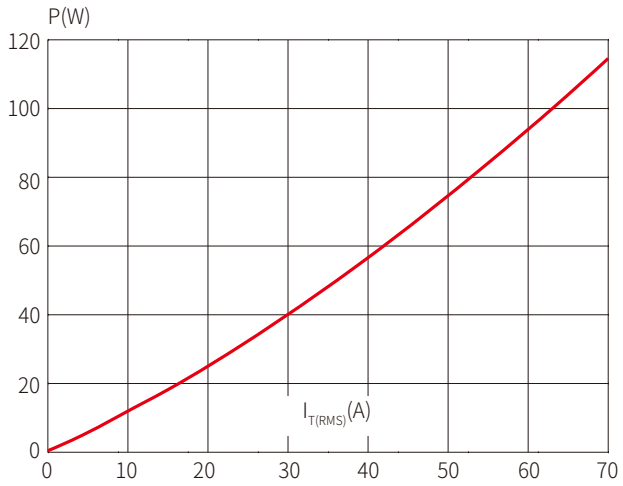


FIG.2: RMS on-state current versus case temperature

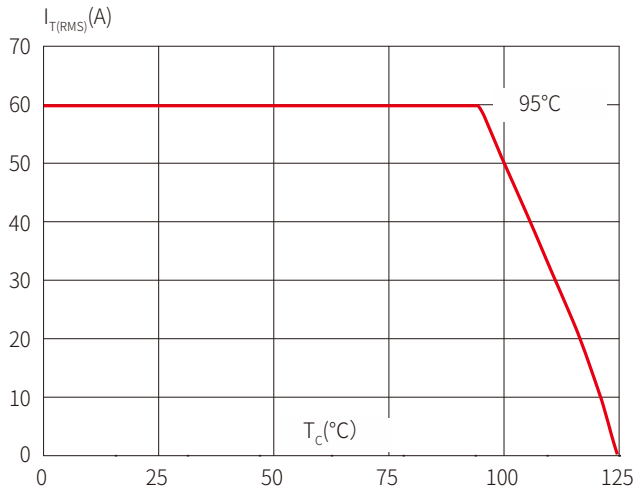


FIG.3: Surge peak on-state current versus number of cycles

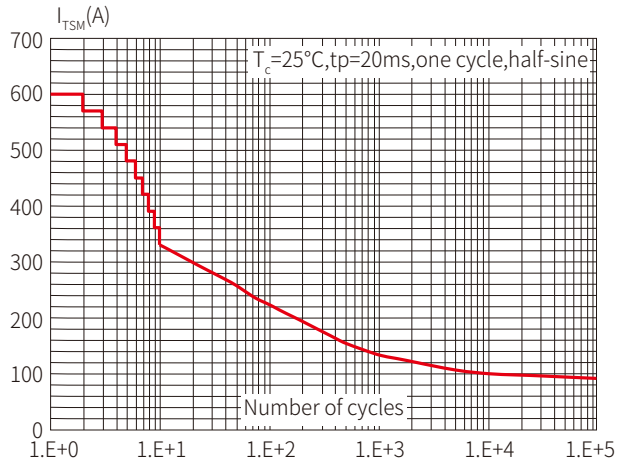


FIG.4 On-state characteristics

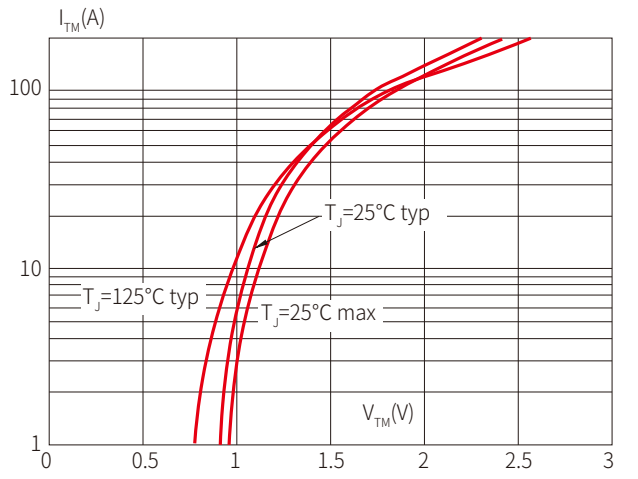


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponding value of I²t (dI/dt<100A/µs)

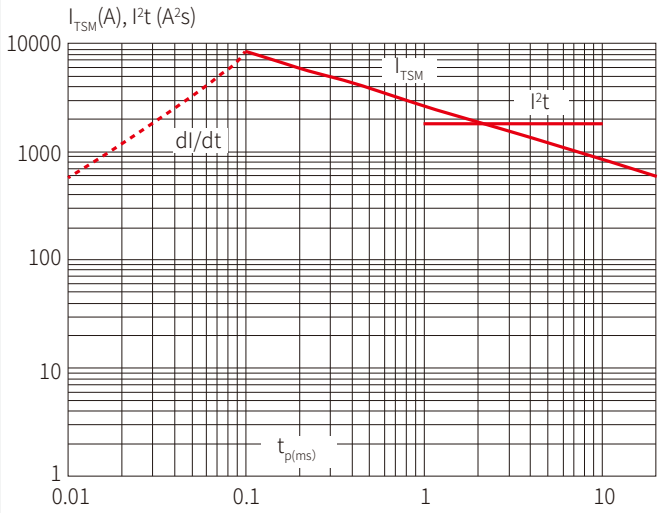
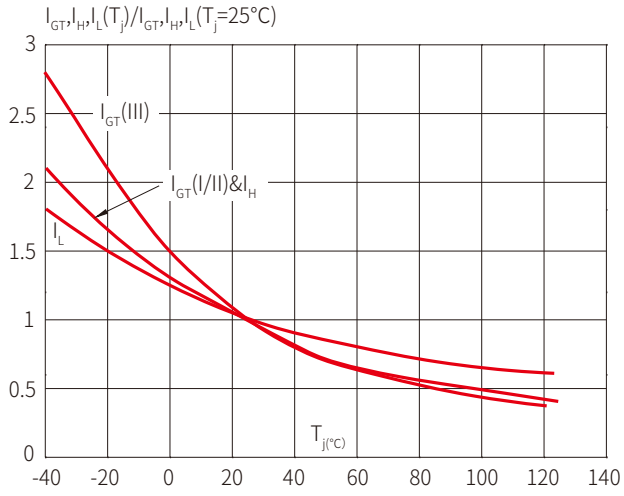


FIG.6 Relative variations of gate trigger current, holding current and latching current versus junction temperature



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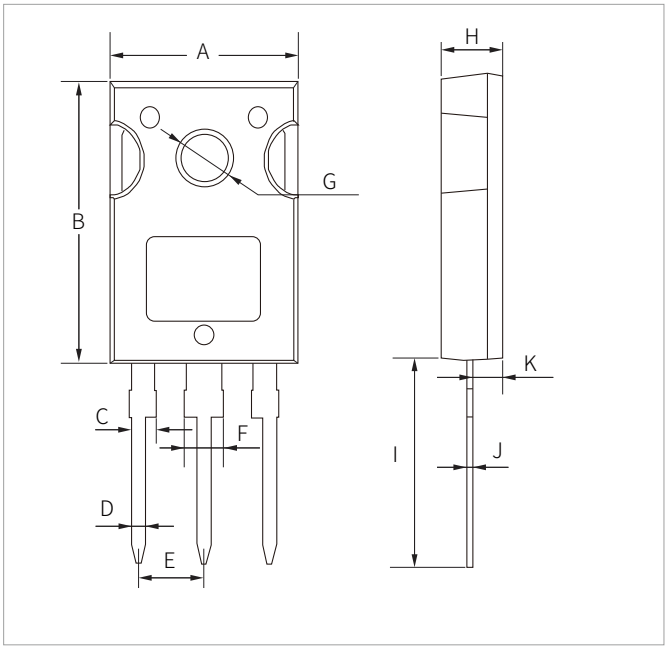

Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	15.4	15.8	0.606	0.662
B	19.5	20.5	0.767	0.807
C	1.8	2.2	0.070	0.087
D	1.15	1.25	0.045	0.050
E	5.2	5.7	0.204	0.225
F	2.8	3.2	0.110	0.126
G	3.4	3.8	0.133	0.149
H	4.8	5.0	0.188	0.204
I	14.0	14.5	0.550	0.570
J	0.4	0.7	0.015	0.029
K	2.4		0.095	

ORDERING INFORMATION

Part Number	Component Package	Marking	QTY/Tube	QTY/Box	QTY/Carton
BTA60-1200BW	TO-247	BTA60-1200BW XXXX	30PCS	450PCS	2250PCS

Headquarters
No.3387 Shendu Road
Pujiang I&E Park
Minhang Shanghai China
201000

Hotline
400-021-5756

Web
Https://www.semiware.com

Sales Center
Tel: 86-21-3463-7458
Email: sales18@semiware.com

Customer Service
Tel: 86-21-5484-1001
Email: sales17@semiware.com

Technical Support
Tel: 86-21-3463-7654
Email: fae01@semiware.com

Complaint & Suggestions
Tel: 86-21-3463-7172
Ext: 8868
Email: cs03@semiware.com

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